DSK Diode Semiconductor Korea **B50D --- B500D**

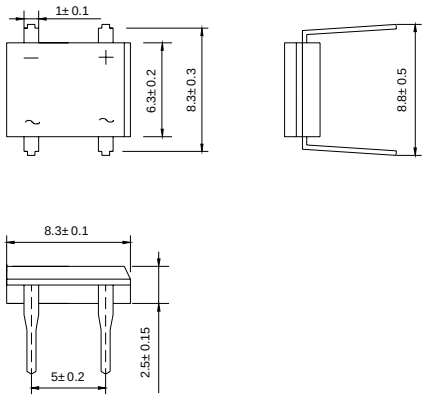
SILICON BRIDGE RECTIFIERS

VOLTAGE RANGE: 80 --- 1000 V
CURRENT: 1.0 A

FEATURES

- ◇ Rating to 1000V PRV
- ◇ Surge overload rating to 40 Amperes peak
- ◇ Ideal for printed circuit board
- ◇ Reliable low cost construction utilizing molded plastic technique results in inexpensive product
- ◇ Solderable per MIL-STD-202 method 208
- ◇ Glass passivated chip junctions
- ◇ Plastic material has UL flammability classification 94V-O
- ◇ Polarity symbols molded on body
- ◇ Weight: 0.016 ounces,0.45 grams

DB - 1



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.
Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

		B40D	B80D	B125D	B250D	B380D	B500D	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	80	160	250	600	800	1000	V
Maximum RMS voltage	V_{RMS}	56	112	175	420	560	700	V
Maximum DC blocking voltage	V_{DC}	80	160	250	600	800	1000	V
Maximum average forw ard Output current @T_A=25℃	$I_{F(AV)}$	1.0						A
Peak forw ard surge current 10ms single half-sine-w ave superimposed on rated load	I_{FSM}	40						A
Maximum instantaneous forw ard voltage at 1.0 A	V_F	1.1						V
Maximum reverse current @T_J=25℃	I_R	10.0						μA
at rated DC blocking voltage @T_J=125℃		0.5						m A
Operating junction temperature range	T_J	- 55 ---- + 150						℃
Storage temperature range	T_{STG}	- 55 ---- + 150						℃

FIG.1 -- PEAK FORWARD SURGE CURRENT

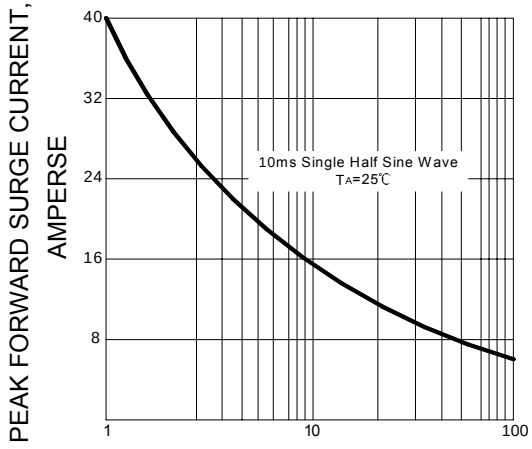


FIG.2 -- FORWARD DERATING CURVE

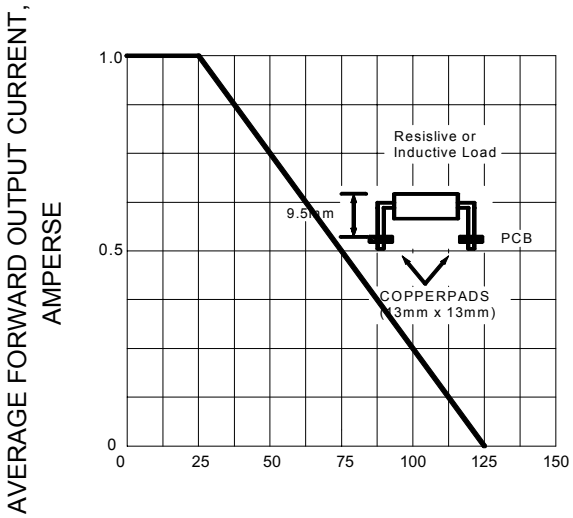


FIG.3 -- TYPICAL FORWARD CHARACTERISTIC

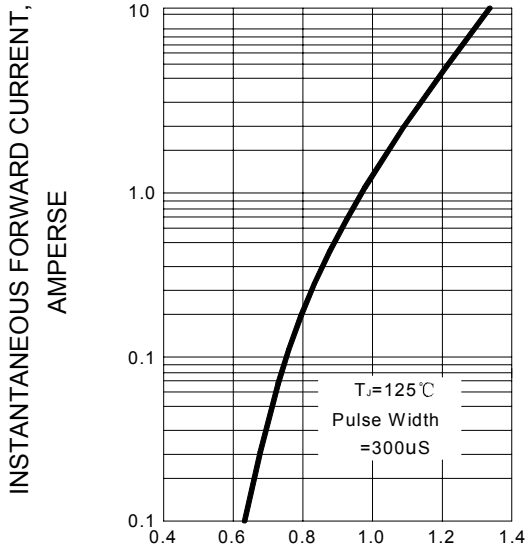


FIG.4 -- TYPICAL REVERSE CHARACTERISTIC

